

FileViewEditToolsWindowHelp

Active  
Failed  
Saved  
    (1) 09/948877  
    (1736) "KONINKLIJKE PHILIPS".as  
    (0) 10/822514  
    (2) 8185803.pn  
    (2374838) parallel\$4  
    (251761) "same" adj2 direction  
    (2494584) parallel\$4 ("same" adj2 direction)  
    (168671) (ferr?electric ferr? adj electric ferr?magnetic ferr? adj magnetic FeRam FF  
    (3503278) first with second  
    (1258099) magnetic  
    (344516) (first with second) with (parallel\$4 ("same" adj2 direction))  
    (81248) (first with second) with magnetic  
    (9191) ((first with second) with (parallel\$4 ("same" adj2 direction))) same ((first with  
    (2455038) (memory cell )  
    (4835504) second  
    (5162555) first  
    (238406) first near4 ((memory cell D)  
    (188789) second near4 ((memory cell D)  
    (96811) (first near4 ((memory cell D)) with (second near4 ((memory cell D))  
    (116) (((first with second) with (parallel\$4 ("same" adj2 direction))) same ((first with  
    (92) (((first with second) with (parallel\$4 ("same" adj2 direction))) same ((first with  
Favorites  
Taoood (1)

BrowseQuitClear

DB:USPAT:US POPUB:EPO:JPO:DERWENT:IBM:TDG

Plerals

Highlight all hit terms initially

Default operator: OR

(((first with second) with (parallel\$4 ("same" adj2 direction))) same ((first with second) with magnetic)) same ((first near4  
(memory cell )  
) with second near4 ((memory cell )  
) and ((ferr?electric ferr? adj electric ferr?magnetic ferr? adj magnetic FeRam FRAM) ((magnetic adj memory mram)  
(magnetoresist\$4 magneto adj resist\$4)) TMR (mtj magnetic adj tunnel adj junction)  
)

June 2004

SPR ItemSPR ItemClipboardTextHTML

#	1	Inventor	Document#	Year	P	Title	Current	Current(XR)	Retrieval	S	C	P	Image	Doc	P
1		Matsuoka, Hi	US 6560135	2003	3	Magnetic semiconductor memory apparatus	365/97	365/171		F	F	F	F	US 656013	
2		Matsuoka, Hi	US 2004010	2004	2	Magnetic semiconductor memory device	365/200			F	F	F	F	US 200401	
3		Sugibayashi,	US 2004010	2004	1	Magnetic memory cell and magnetic random	365/200			F	F	F	F	US 200401	
4		Heide, Carste	US 2004007	2004	2	Magnetic memory device	365/173			F	F	F	F	US 200400	
5		Odagawa, Ak	US 2004005	2004	6	Magnetoresistance element and magnetoresi	360/324	365/158		F	F	F	F	US 200400	
6		Hung, Chien-	US 2004004	2004	2	High density magnetic random access memor	365/202			F	F	F	F	US 200400	
7		Asao, Yoshie	US 2004000	2004	2	Magnetic random access memory	365/222			F	F	F	F	US 200400	
8		Ooishi, Tsuka	US 2003023	2003	5	Thin film magnetic memory device and semic	365/158			F	F	F	F	US 200302	
9		Hideaki, Hidet	US 2003022	2003	1	Thin film magnetic memory device having re	365/171			F	F	F	F	US 200302	
10		Perner, Frede	US 2003021	2003	1	Magnetoresistive random access memory (M	365/202			F	F	F	F	US 200302	

Ready